

Abstract

Cu ALLOY BONDING WIRE FOR SEMICONDUCTOR DEVICE

It is an object to provide a Cu alloy bonding wire for a semiconductor device that can satisfy required performance in high-density LSI applications. In the Cu alloy bonding wire for a semiconductor device according to the present invention, each of abundance ratios of crystal orientations $\langle 100 \rangle$, $\langle 110 \rangle$ and $\langle 111 \rangle$ having an angular difference of 15 degrees or less from a direction perpendicular to one plane including a wire center axis out of crystal orientations on a wire surface is 3% or more and less than 27% in average area percentage.

FIG. 3